

## 2SA928 PNP Silicon Epitaxial Planar Transistor

for audio power amplifier

The transistor is subdivided into two groups, O and Y, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base  
TO-92 Plastic Package  
Weight approx. 0.18g

### Absolute Maximum Ratings (Ta=25°C)

	Symbol	Value	Unit
Collector to Base Voltage	$-V_{CBO}$	30	V
Collector to Emitter Voltage	$-V_{CEO}$	30	V
Emitter to Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	2	A
Power Dissipation	$P_{tot}$	1	W
Operating and Storage Junction Temperature	$T_j, T_s$	-55 to +150	°C



### Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE}=2\text{V}$ , $-I_C=500\text{mA}$	O	$h_{FE}$	100	-	200	-
	Y	$h_{FE}$	160	-	320	-
Collector Cutoff Current at $-V_{CB}=30\text{V}$	$-I_{CBO}$	-	-	0.1	$\mu\text{A}$	
Emitter Cutoff Current at $-V_{EB}=5\text{V}$	$-I_{EBO}$	-	-	0.1	$\mu\text{A}$	
Collector-Emitter Breakdown Voltage at $-I_C=10\text{mA}$	$-V_{(BR)CEO}$	30	-	-	V	
Collector-Base Breakdown Voltage at $-I_C=100\mu\text{A}$	$-V_{(BR)CBO}$	30	-	-	V	
Emitter-Base Breakdown Voltage at $-I_E=1\text{mA}$	$-V_{(BR)EBO}$	5	-	-	V	
Output Capacitance at $-V_{CB}=10\text{V}$ , $f=1\text{MHz}$	Cob	-	48	-	pF	
Collector to Emitter Saturation Voltage at $-I_C=1.5\text{A}$ , $-I_B=0.03\text{A}$	$-V_{CE(sat)}$	-	-	2	V	
Base-Emitter Voltage at $-V_{CE}=2\text{V}$ , $-I_C=500\text{mA}$	$-V_{BE}$	-	-	1	V	
Transition Frequency at $-V_{CE}=2\text{V}$ , $-I_C=500\text{mA}$	$f_T$	-	120	-	MHz	